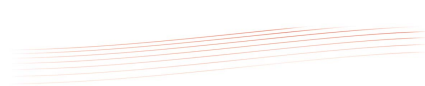


August 3, 2004

ATI Radeon™ 9600XT Graphic Processor Structural Analysis

(Black Diamond™ Low-k Dielectrics and Diagonal Routing Architecture)



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